

HiPerFET™

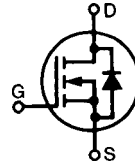
Power MOSFETs

IXFH/IXFM6N90
IXFH/IXFM6N100

N-Channel Enhancement Mode
High dv/dt, Low t_{rr} , HDMOS™ Family

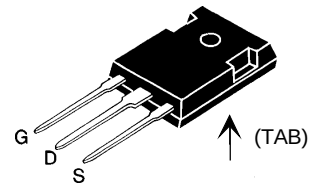
V_{DSS}	I_{D25}	$R_{DS(on)}$
900 V	6 A	1.8 Ω
1000 V	6 A	2.0 Ω

$$t_{rr} \leq 250 \text{ ns}$$

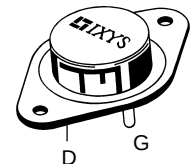


Symbol	Test Conditions	Maximum Ratings		
V_{DSS}	$T_J = 25^\circ\text{C}$ to 150°C	6N90	900	V
V_{DGR}	$T_J = 25^\circ\text{C}$ to 150°C ; $R_{GS} = 1 \text{ M}\Omega$		1000	V
V_{GS}	Continuous		± 20	V
V_{GSM}	Transient		± 30	V
I_{D25}	$T_C = 25^\circ\text{C}$		6	A
I_{DM}	$T_C = 25^\circ\text{C}$, pulse width limited by T_{JM}		24	A
I_{AR}	$T_C = 25^\circ\text{C}$		6	A
E_{AR}	$T_C = 25^\circ\text{C}$		18	mJ
dv/dt	$I_S \leq I_{DM}$, $di/dt \leq 100 \text{ A}/\mu\text{s}$, $V_{DD} \leq V_{DSS}$, $T_J \leq 150^\circ\text{C}$, $R_G = 2 \Omega$		5	V/ns
P_D	$T_C = 25^\circ\text{C}$		180	W
T_J			-55 ... +150	$^\circ\text{C}$
T_{JM}			150	$^\circ\text{C}$
T_{stg}			-55 ... +150	$^\circ\text{C}$
T_L	1.6 mm (0.062 in.) from case for 10 s		300	$^\circ\text{C}$
M_d	Mounting torque		1.13/10	Nm/lb.in.
Weight			TO-204 = 18 g, TO-247 = 6 g	

TO-247 AD (IXFH)



TO-204 AA (IXFM)



G = Gate, D = Drain,
S = Source, TAB = Drain

Features

- International standard packages
- Low $R_{DS(on)}$ HDMOS™ process
- Rugged polysilicon gate cell structure
- Unclamped Inductive Switching (UIS) rated
- Low package inductance
 - easy to drive and to protect
- Fast intrinsic Rectifier

Applications

- DC-DC converters
- Synchronous rectification
- Battery chargers
- Switched-mode and resonant-mode power supplies
- DC choppers
- AC motor control
- Temperature and lighting controls
- Low voltage relays

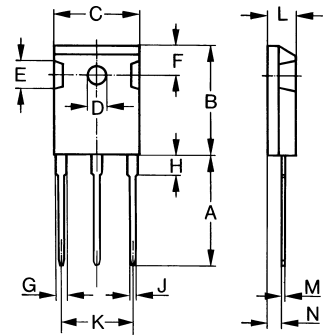
Advantages

- Easy to mount with 1 screw (TO-247) (isolated mounting screw hole)
- Space savings
- High power density

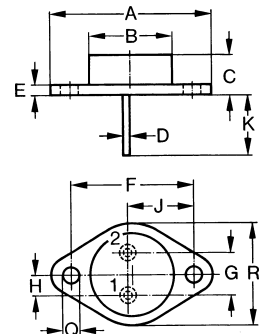
Symbol	Test Conditions	Characteristic Values (T _j = 25°C, unless otherwise specified)			
			min.	typ.	max.
V _{DSS}	V _{GS} = 0 V, I _D = 3 mA	6N90	900		V
		6N100	1000		V
V _{GS(th)}	V _{DS} = V _{GS} , I _D = 2.5 mA		2.0		4.5 V
I _{GSS}	V _{GS} = ±20 V _{DC} , V _{DS} = 0				±100 nA
I _{DSS}	V _{DS} = 0.8 • V _{DSS}	T _j = 25°C			250 μA
	V _{GS} = 0 V	T _j = 125°C			1 mA
R _{DS(on)}	V _{GS} = 10 V, I _D = 0.5 • I _{D25}	6N90			1.8 Ω
		6N100			2.0 Ω
	Pulse test, t ≤ 300 μs, duty cycle d ≤ 2 %				

Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
g_{fs}	$V_{DS} = 10\text{ V}$; $I_D = 0.5 \cdot I_{D25}$, pulse test	4	6	S
C_{iss}	$V_{GS} = 0\text{ V}$, $V_{DS} = 25\text{ V}$, $f = 1\text{ MHz}$		2600	pF
C_{oss}			180	pF
C_{rss}			45	pF
$t_{d(on)}$	$V_{GS} = 10\text{ V}$, $V_{DS} = 0.5 \cdot V_{DSS}$, $I_D = 0.5 \cdot I_{D25}$ $R_G = 4.7\ \Omega$ (External)		35	100 ns
t_r			40	110 ns
$t_{d(off)}$			100	200 ns
t_f			60	100 ns
$Q_{g(on)}$	$V_{GS} = 10\text{ V}$, $V_{DS} = 0.5 \cdot V_{DSS}$, $I_D = 0.5 \cdot I_{D25}$		88	130 nC
Q_{gs}			21	30 nC
Q_{gd}			38	70 nC
R_{thJC}			0.25	0.7 K/W
R_{thCK}				K/W

Source-Drain Diode		Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
Symbol	Test Conditions	min.	typ.	max.
I_S	$V_{GS} = 0\text{ V}$			6 A
I_{SM}	Repetitive; pulse width limited by T_{JM}			24 A
V_{SD}	$I_F = I_S$, $V_{GS} = 0\text{ V}$, Pulse test, $t \leq 300\ \mu\text{s}$, duty cycle $d \leq 2\%$			1.5 V
t_{rr}	$I_F = I_S$ $-di/dt = 100\text{ A}/\mu\text{s}$, $V_R = 100\text{ V}$	$T_J = 25^\circ\text{C}$		250 ns
		$T_J = 125^\circ\text{C}$		400 ns
Q_{RM}		$T_J = 25^\circ\text{C}$		0.5 μC
		$T_J = 125^\circ\text{C}$		1.0 μC
I_{RM}		$T_J = 25^\circ\text{C}$		7.5 A
		$T_J = 125^\circ\text{C}$		9.0 A

TO-247 AD (IXFH) Outline


Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	19.81	20.32	0.780	0.800
B	20.80	21.46	0.819	0.845
C	15.75	16.26	0.610	0.640
D	3.55	3.65	0.140	0.144
E	4.32	5.49	0.170	0.216
F	5.4	6.2	0.212	0.244
G	1.65	2.13	0.065	0.084
H	-	4.5	-	0.177
J	1.0	1.4	0.040	0.055
K	10.8	11.0	0.426	0.433
L	4.7	5.3	0.185	0.209
M	0.4	0.8	0.016	0.031
N	1.5	2.49	0.087	0.102

TO-204 AA (IXFM) Outline


Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	38.61	39.12	1.520	1.540
B	19.43	19.94	-	0.785
C	6.40	9.14	0.252	0.360
D	0.97	1.09	0.038	0.043
E	1.53	2.92	0.060	0.115
F	30.15	BSC	1.187	BSC
G	10.67	11.17	0.420	0.440
H	5.21	5.71	0.205	0.225
J	16.64	17.14	0.655	0.675
K	11.18	12.19	0.440	0.480
Q	3.84	4.19	0.151	0.165
R	25.16	25.90	0.991	1.020

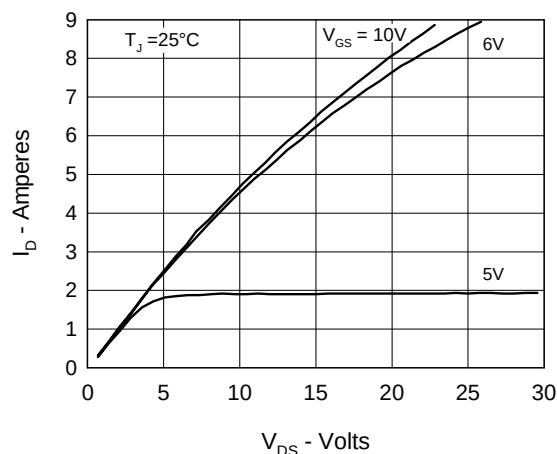
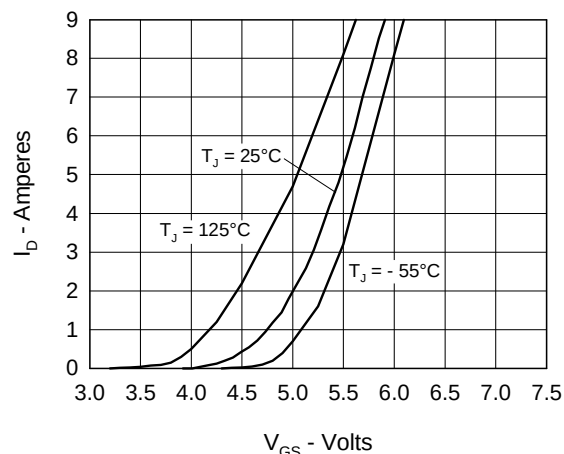
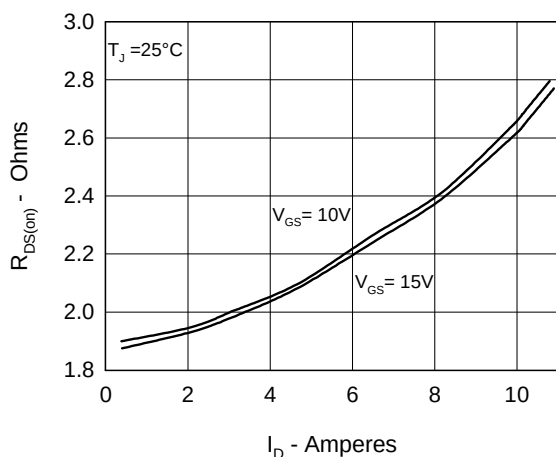
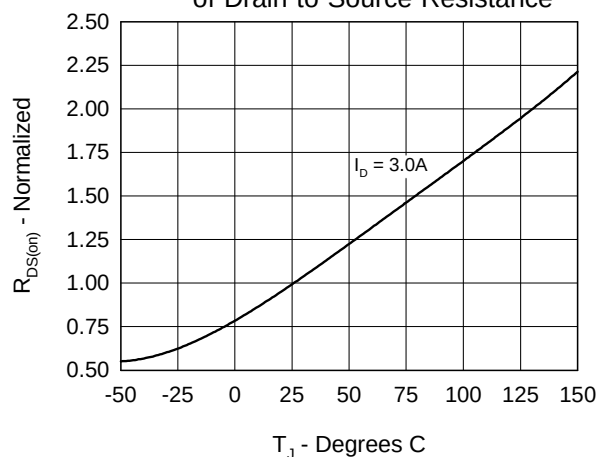
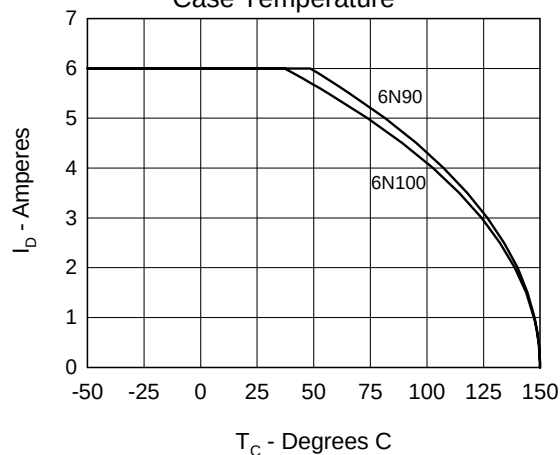
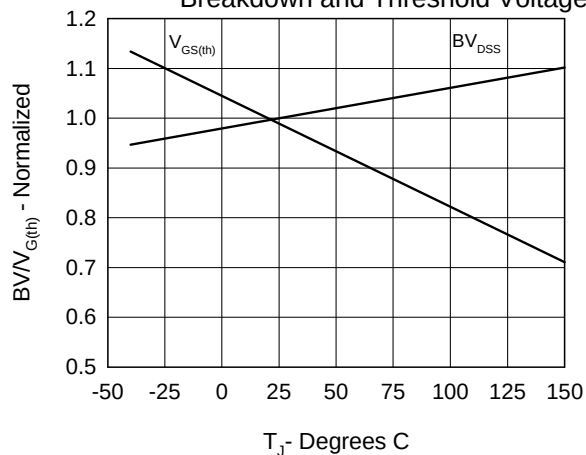
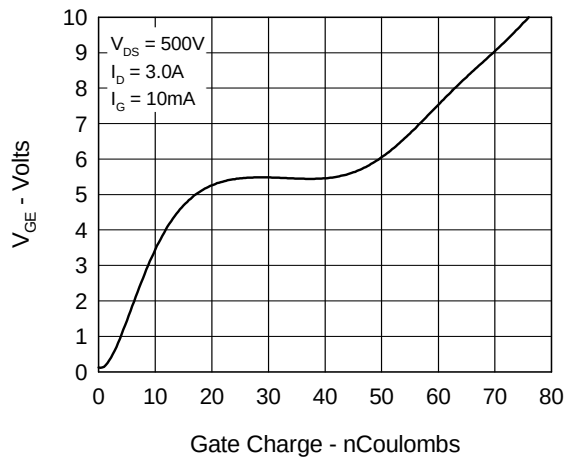
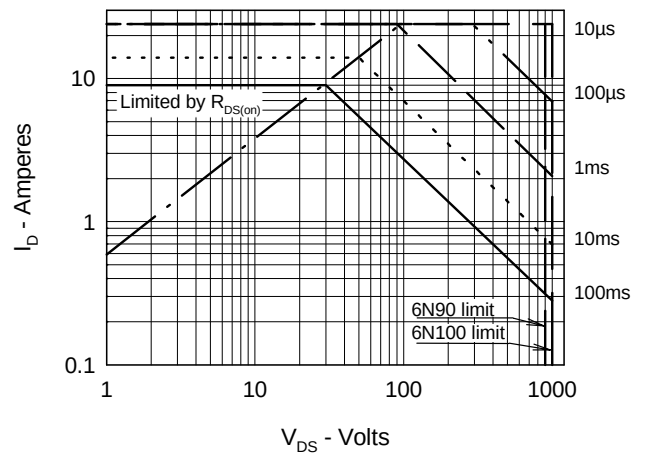
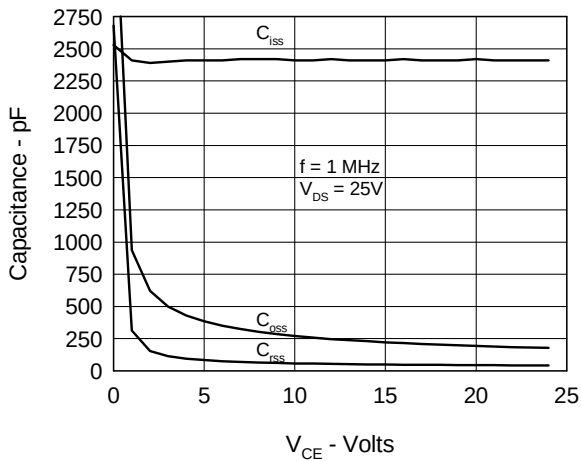
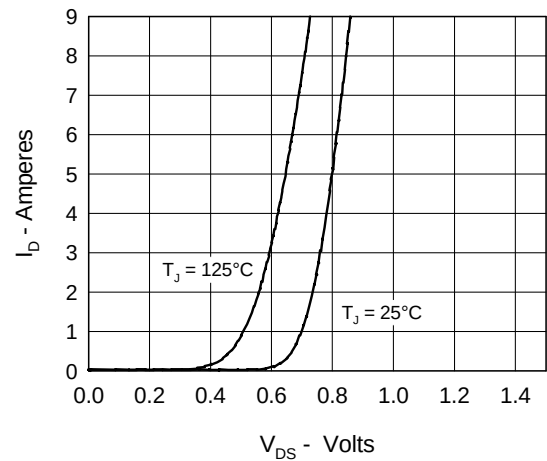
Fig. 1 Output Characteristics

Fig. 2 Input Admittance

Fig. 3 $R_{DS(on)}$ vs. Drain Current

Fig. 4 Temperature Dependence of Drain to Source Resistance

Fig. 5 Drain Current vs. Case Temperature

Fig. 6 Temperature Dependence of Breakdown and Threshold Voltage


Fig.7 Gate Charge Characteristic Curve

Fig.8 Forward Bias Safe Operating Area

Fig.9 Capacitance Curves

Fig.10 Source Current vs. Source to Drain Voltage

Fig.11 Transient Thermal Impedance
